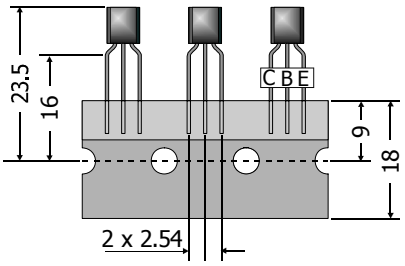
Diotec Semiconductor

BC546 ... BC549

NPN **General Purpose Si-Epitaxial Planar Transistors**
Si-Epitaxial Planar-Transistoren für universellen Einsatz **NPN**

Version 2006-05-31



Dimensions - Maße [mm]

Power dissipation – Verlustleistung	500 mW
Plastic case Kunststoffgehäuse	TO-92 (10D3)
Weight approx. – Gewicht ca.	0.18 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging taped in ammo pack Standard Lieferform gegurtet in Ammo-Pack	

Maximum ratings (T_A = 25°C) **Grenzwerte (T_A = 25°C)**

			BC546	BC547	BC548/ 549
Collector-Emitter-voltage	E-B short	V_{CES}	85 V	50 V	30 V
Collector-Emitter-voltage	B open	V_{CEO}	65 V	45 V	30 V
Collector-Base-voltage	E open	V_{CBO}	80 V	50 V	30 V
Emitter-Base-voltage	C open	V_{EB0}	5 V		
Power dissipation – Verlustleistung		P_{tot}	500 mW [1])		
Collector current – Kollektorstrom (dc)		I_C	100 mA		
Peak Collector current – Kollektor-Spitzenstrom		I_{CM}	200 mA		
Peak Base current – Basis-Spitzenstrom		I_{BM}	200 mA		
Peak Emitter current – Emitter-Spitzenstrom		$-I_{EM}$	200 mA		
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-55...+150°C -55...+150°C		

Characteristics (T_j = 25°C) **Kennwerte (T_j = 25°C)**

		Group A	Group B	Group C
DC current gain – Kollektor-Basis-Stromverhältnis [2])				
V_{CE} = 5 V, I_C = 10 µA	h_{FE}	typ. 90	typ. 150	typ. 270
V_{CE} = 5 V, I_C = 2 mA	h_{FE}	110 ... 220	200 ... 450	420 ... 800
V_{CE} = 5 V, I_C = 100 mA	h_{FE}	typ. 120	typ. 200	typ. 400
h-Parameters at/bei V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz				
Small signal current gain Kleinsignal-Stromverstärkung	h_{fe}	typ. 220	typ. 330	typ. 600
Input impedance – Eingangs-Impedanz	h_{ie}	1.6 ... 4.5 kΩ	3.2 ...8.5 kΩ	6 ... 15 kΩ
Output admittance – Ausgangs-Leitwert	h_{oe}	18 < 30 µS	30 < 60 µS	60 < 110 µS
Reverser voltage transfer ratio Spannungsrückwirkung	h_{re}	typ. $1.5*10^{-4}$	typ. $2*10^{-4}$	typ. $3*10^{-4}$

1 Valid, if leads are kept at ambient temperature at a distance of 2 mm from case
Gültig wenn die Anschlussdrähte in 2 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

Characteristics (T_j = 25°C) **Kennwerte (T_j = 25°C)**

			Min.	Typ.	Max.
Collector-Emitter cutoff current – Kollektor-Emitter-Reststrom					
V_{CE} = 80 V, (B-E short)	BC546	I_{CES}	–	0.2 nA	15 nA
V_{CE} = 50 V, (B-E short)	BC547	I_{CES}	–	0.2 nA	15 nA
V_{CE} = 30 V, (B-E short)	BC548 / BC549	I_{CES}	–	0.2 nA	15 nA
V_{CE} = 80 V, T_j = 125°C, (B-E short)	BC546	I_{CES}	–	–	4 µA
V_{CE} = 50 V, T_j = 125°C, (B-E short)	BC547	I_{CES}	–	–	4 µA
V_{CE} = 30 V, T_j = 125°C, (B-E short)	BC548 / BC549	I_{CES}	–	–	4 µA
Collector-Emitter saturation voltage – Kollektor-EmitterSättigungsspg. [2]					
I_C = 10 mA, I_B = 0.5 mA		V_{CEsat}	–	80 mV	200 mV
I_C = 100 mA, I_B = 5 mA		V_{CEsat}	–	200 mV	600 mV
Base saturation voltage – Basis-Sättigungsspannung [2]					
I_C = 10 mA, I_B = 0.5 mA		V_{BEsat}	–	700 mV	–
I_C = 100 mA, I_B = 5 mA		V_{BEsat}	–	900 mV	–
Base-Emitter-voltage – Basis-Emitter-Spannung [2]					
V_{CE} = 5 V, I_C = 2 mA		V_{BE}	580 mV	660 mV	700 mV
V_{CE} = 5 V, I_C = 10 mA		V_{BE}	–	–	720 mV
Gain-Bandwidth Product – Transitfrequenz					
V_{CE} = 5 V, I_C = 10 mA, f = 100 MHz		f_T	–	300 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität					
V_{CB} = 10 V, I_E = i_e = 0, f = 1 MHz		C_{CBO}	–	3.5 pF	6 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität					
V_{EB} = 0.5 V, I_C = i_c = 0, f = 1 MHz		C_{EB0}	–	9 pF	–
Noise figure – Rauschzahl					
V_{CE} = 5 V, I_C = 200 µA, R_G = 2 kΩ	BC546 / BC547	F	–	2 dB	10 dB
f = 1 kHz, Δf = 200 Hz	BC548 / BC549	F	–	1.2 dB	4 dB
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft		R_{thA}	< 200 K/W [1]		
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren			BC556 ... BC559		
Available current gain groups per type Lieferbare Stromverstärkungsgruppen pro Typ			BC546A BC547A BC548A	BC546B BC547B BC548B BC549B	 BC547C BC548C BC549C

2 Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

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